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Supporting Information

Fully Solution-Induced Ultralow Voltage High Performance Indium Oxide Thin Film Transistors With ZrO_x High-k Gate Dielectrics

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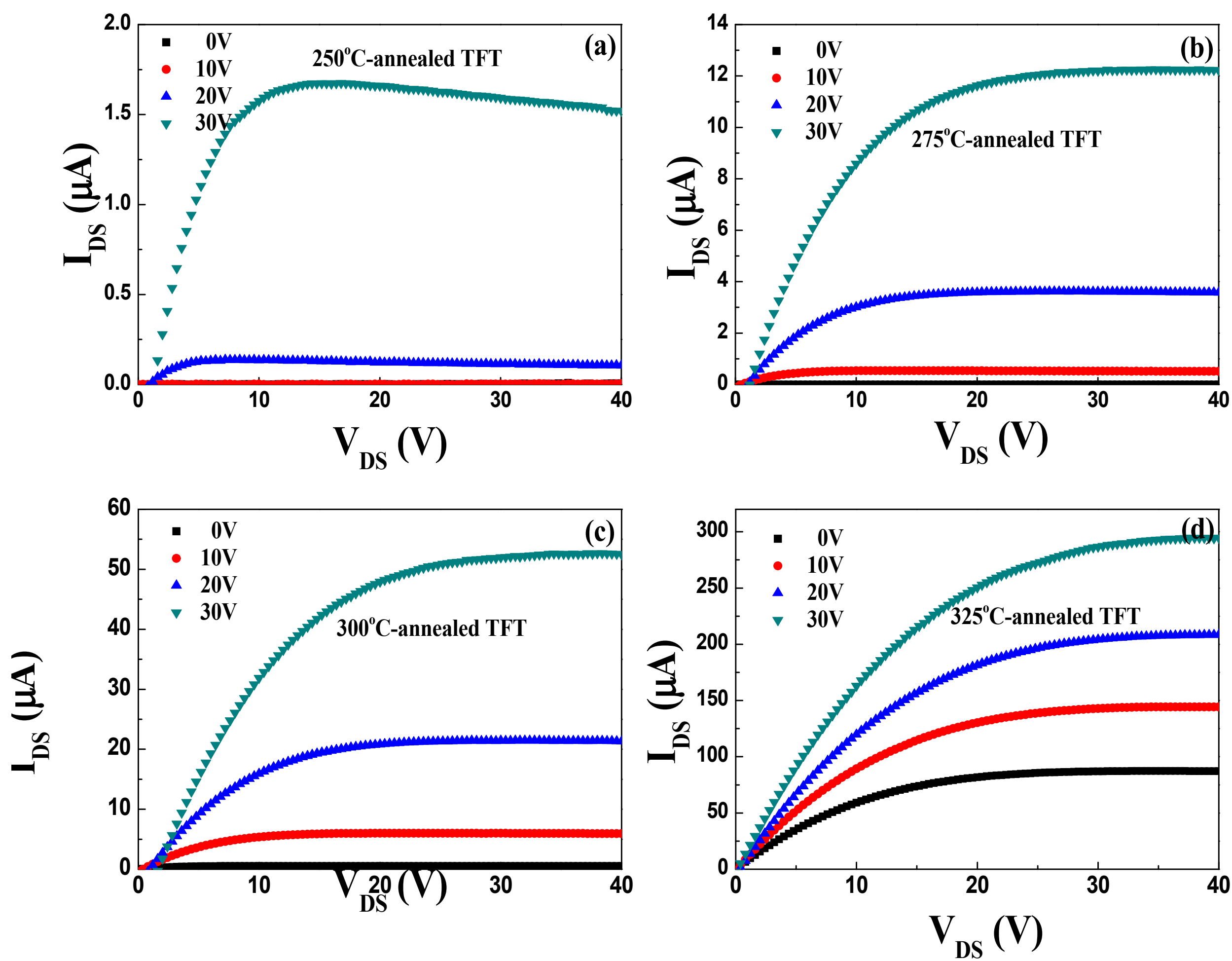

Figure S1. The output characteristics of the (a) 250°C-annealed In_2O_3/SiO_2 TFTs, (b) 275°C-annealed In_2O_3/SiO_2 TFTs, (c) 300°C-annealed In_2O_3/SiO_2 TFTs, (d) 325°C-annealed In_2O_3/SiO_2 TFTs.

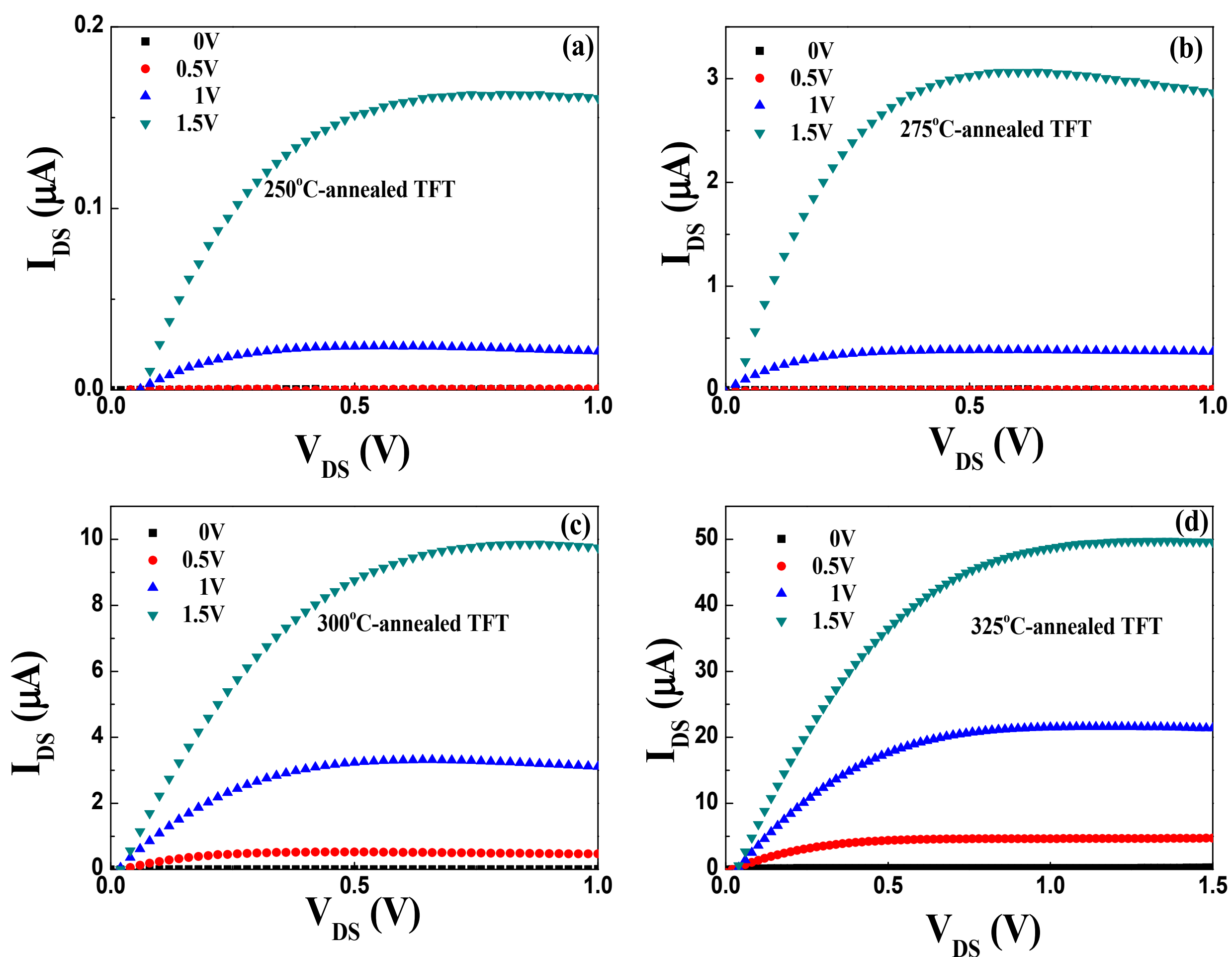

Figure S2. The output characteristics of the (a) 250°C-annealed In_2O_3/ZrO_x TFTs, (b) 275°C-annealed In_2O_3/ZrO_x TFTs, (c) 300°C-annealed In_2O_3/ZrO_x TFTs, (d) 325°C-annealed In_2O_3/ZrO_x TFTs.